

ABSTRACT OF THE DISCLOSURE

A radiation-sensitive resin composition comprising (A)  
a photoacid generator such as  
2,4,6-trimethylphenyldiphenylsulfonium  
5 2,4-difluorobenzenesulfonate or  
2,4,6-trimethylphenyldiphenylsulfonium  
4-trifluoromethylbenzenesulfonate and (B) a resin having an  
acetal structure typified by a poly(p-hydroxystyrene) resin in  
which a part of hydrogen atoms of phenolic hydroxyl groups have  
10 been replaced by 1-ethoxyethyl groups, 1-ethoxyethyl groups and  
t-butoxycarbonyl groups, or 1-ethoxyethyl groups and t-butyl  
groups. The resin composition is sensitive to deep ultraviolet  
rays and charged particles such as electron beams, exhibits  
excellent resolution performance and pattern shape-forming  
15 capability, and suppresses a nano-edge roughness phenomenon to  
a minimal extent.